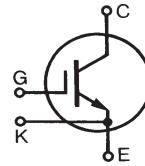


# GenX3™ 600V IGBT

# IXGN200N60B3

Medium-Speed Low-V<sub>sat</sub> PT IGBT for 5-40kHz Switching

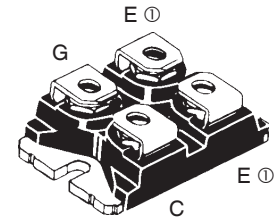


$$V_{CES} = 600V$$

$$I_{C110} = 200A$$

$$V_{CE(sat)} \leq 1.50V$$

SOT-227B, miniBLOC  
 E153432



G = Gate, C = Collector, E = Emitter  
 ① Either Emitter Terminal can be used as Main or Kelvin Emitter

| Symbol         | Test Conditions   | Maximum Ratings       |            |
|----------------|---|-----------------------|------------|
| $V_{CES}$      | $T_J = 25^\circ C$ to $150^\circ C$                       | 600                   | V          |
| $V_{CGR}$      | $T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$ | 600                   | V          |
| $V_{GES}$      | Continuous  | $\pm 20$              | V          |
| $V_{GEM}$      | Transient   | $\pm 30$              | V          |
| $I_{C25}$      | $T_C = 25^\circ C$  | 300                   | A          |
| $I_{C110}$     | $T_C = 110^\circ C$                                       | 200                   | A          |
| $I_{LRMS}$     | Terminal Current Limit                                    | 200                   | A          |
| $I_{CM}$       | $T_C = 25^\circ C$ , 1ms                                  | 1200                  | A          |
| <b>SSOA</b>    | $V_{GE} = 15V$ , $T_{VJ} = 125^\circ C$ , $R_G = 1\Omega$ | $I_{CM} = 300$        | A          |
| <b>(RBSOA)</b> | Clamped Inductive Load                                    | $V_{CE} \leq V_{CES}$ |            |
| $P_C$          | $T_C = 25^\circ C$  | 830                   | W          |
| $T_J$          |   | - 55 ... +150         | $^\circ C$ |
| $T_{JM}$       |   | 150                   | $^\circ C$ |
| $T_{stg}$      |   | - 55 ... +150         | $^\circ C$ |
| $V_{ISOL}$     | 50/60Hz   | $t = 1min$            | 2500 V~    |
|                | $I_{ISOL} \leq 1mA$                                       | $t = 1s$              | 3000 V~    |
| $M_d$          | Mounting Torque   | 1.5/13                | Nm/lb.in.  |
|                | Terminal Connection Torque (M4)                           | 1.3/11.5              | Nm/lb.in.  |
| <b>Weight</b>  |   | 30                    | g          |

## Features

- International Standard Package miniBLOC
- UL Recognized
- Aluminium Nitride Isolation
  - High Power Dissipation
- Isolation Voltage 3000 V~
- Very High Current IGBT
- Low  $V_{CE(sat)}$  for Minimum on-state Conduction Losses
- MOS Gate Turn-On
  - Drive Simplicity
- Low Collector-to-Case Capacitance (< 50 pF)
- Low Package Inductance (< 5 nH)
  - Easy to Drive and to Protect

## Advantages

- High Power Density
- Low Gate Drive Requirement

## Applications

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- DC Choppers
- AC Motor Speed Drives
- DC Servo and Robot Drives

| Symbol        | Test Conditions<br>( $T_J = 25^\circ C$ , Unless Otherwise Specified)           | Characteristic Values |      |                    |
|---------------|---|-----------------------|------|--------------------|
|               |   | Min.                  | Typ. | Max.               |
| $V_{GE(th)}$  | $I_C = 250\mu A$ , $V_{CE} = V_{GE}$  | 3.0                   |      | 5.0 V              |
| $I_{CES}$     | $V_{CE} = V_{CES}$ , $V_{GE} = 0V$<br>$T_J = 125^\circ C$                       |                       |      | 50 $\mu A$<br>5 mA |
| $I_{GES}$     | $V_{CE} = 0V$ , $V_{GE} = \pm 20V$  |                       |      | $\pm 100$ nA       |
| $V_{CE(sat)}$ | $I_C = 100A$ , $V_{GE} = 15V$ , Note 1<br>$I_C = 200A$ ,<br>$T_J = 125^\circ C$ | 1.35                  | 1.50 | V                  |
|               |   | 1.65                  |      | V                  |
|               |   | 1.75                  |      | V                  |

| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)  | Characteristic Values |      |                         |
|--------------|--|-----------------------|------|-------------------------|
|              |  | Min.                  | Typ. | Max.                    |
| $g_{fs}$     | $I_C = 60\text{A}, V_{CE} = 10\text{V}$ , Note 1   | 95                    | 160  | S                       |
| $C_{ies}$    | $V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$   |                       | 26   | nF                      |
| $C_{oes}$    |  |                       | 1260 | pF                      |
| $C_{res}$    |  |                       | 97   | pF                      |
| $Q_{g(on)}$  | $I_C = 100\text{V}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$   |                       | 750  | nC                      |
| $Q_{ge}$     |  |                       | 115  | nC                      |
| $Q_{gc}$     |  |                       | 245  | nC                      |
| $t_{d(on)}$  | <b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b><br>$I_C = 100\text{A}, V_{GE} = 15\text{V}$<br>$V_{CE} = 300\text{V}, R_G = 1\Omega$  |                       | 44   | ns                      |
| $t_{ri}$     |  |                       | 83   | ns                      |
| $E_{on}$     |  |                       | 1.6  | mJ                      |
| $t_{d(off)}$ |  |                       | 310  | 450 ns                  |
| $t_{fi}$     |  |                       | 183  | 300 ns                  |
| $E_{off}$    |  |                       | 2.9  | 4.5 mJ                  |
| $t_{d(on)}$  | <b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b><br>$I_C = 100\text{A}, V_{GE} = 15\text{V}$<br>$V_{CE} = 300\text{V}, R_G = 1\Omega$ |                       | 42   | ns                      |
| $t_{ri}$     |  |                       | 80   | ns                      |
| $E_{on}$     |  |                       | 2.4  | mJ                      |
| $t_{d(off)}$ |  |                       | 430  | ns                      |
| $t_{fi}$     |  |                       | 300  | ns                      |
| $E_{off}$    |  |                       | 4.2  | mJ                      |
| $R_{thJC}$   |  |                       |      | 0.15 $^\circ\text{C/W}$ |
| $R_{thCK}$   |  | 0.05                  |      | $^\circ\text{C/W}$      |

### SOT-227B miniBLOC



| SYM | INCHES |       | MILLIMETERS |       |
|-----|--------|-------|-------------|-------|
|     | MIN    | MAX   | MIN         | MAX   |
| A   | 1.240  | 1.255 | 31.50       | 31.88 |
| B   | .307   | .323  | 7.80        | 8.20  |
| C   | .161   | .169  | 4.09        | 4.29  |
| D   | .161   | .169  | 4.09        | 4.29  |
| E   | .161   | .169  | 4.09        | 4.29  |
| F   | .587   | .595  | 14.91       | 15.11 |
| G   | 1.186  | 1.193 | 30.12       | 30.30 |
| H   | 1.496  | 1.505 | 38.00       | 38.23 |
| J   | .460   | .481  | 11.68       | 12.22 |
| K   | .351   | .378  | 8.92        | 9.60  |
| L   | .030   | .033  | 0.76        | 0.84  |
| M   | .496   | .506  | 12.60       | 12.85 |
| N   | .990   | 1.001 | 25.15       | 25.42 |
| O   | .078   | .084  | 1.98        | 2.13  |
| P   | .195   | .235  | 4.95        | 5.97  |
| Q   | 1.045  | 1.059 | 26.54       | 26.90 |
| R   | .155   | .174  | 3.94        | 4.42  |
| S   | .186   | .191  | 4.72        | 4.85  |
| T   | .968   | .987  | 24.59       | 25.07 |
| U   | -.002  | .004  | -0.05       | 0.1   |

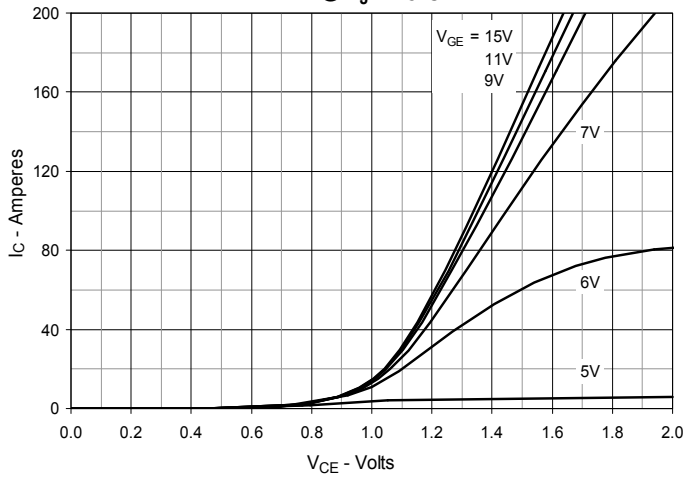
Note 1. Pulse test,  $t \leq 300\mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .

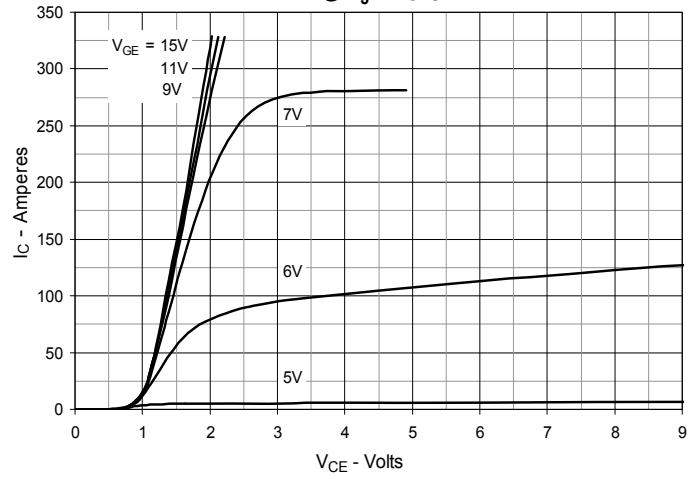
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

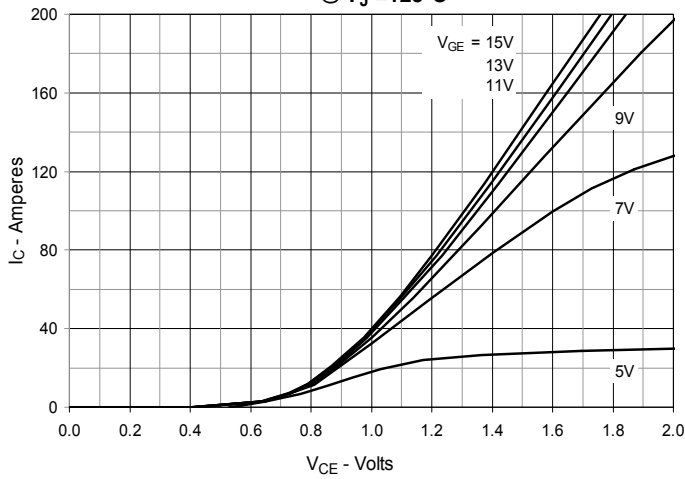
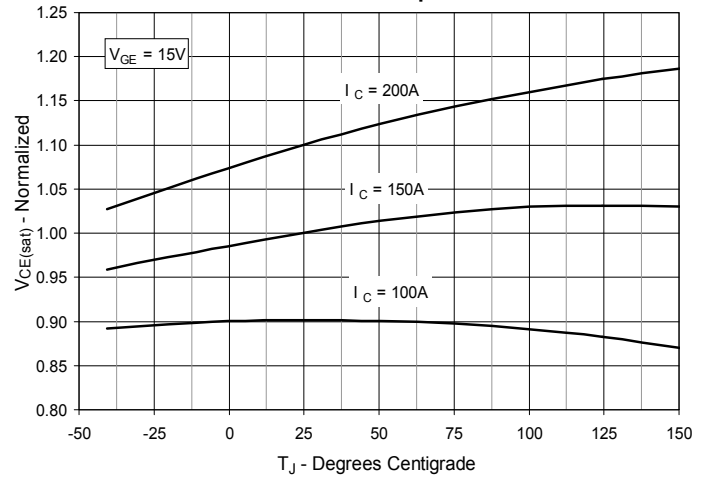
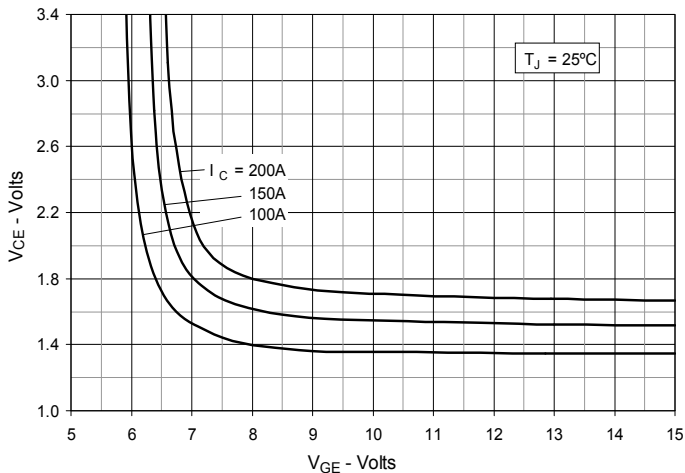
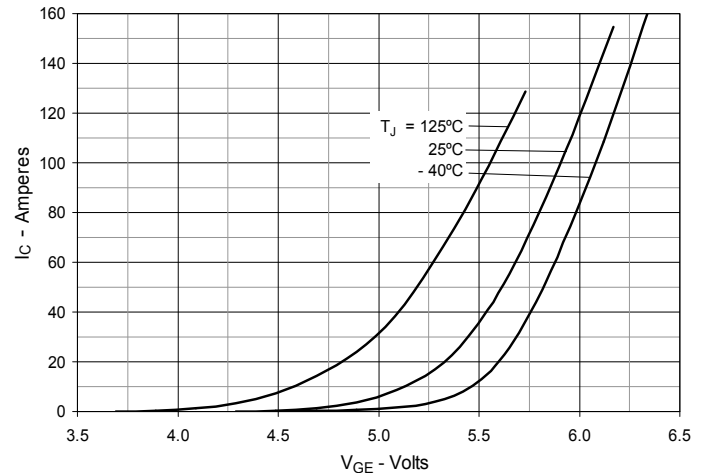
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

|           |           |           |           |              |              |              |              |              |             |
|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665    | 6,404,065 B1 | 6,683,344    | 6,727,585    | 7,005,734 B2 | 7,157,338B2 |
| 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343    | 6,710,405 B2 | 6,759,692    | 7,063,975 B2 |             |
| 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505    | 6,710,463    | 6,771,478 B2 | 7,071,537    |             |

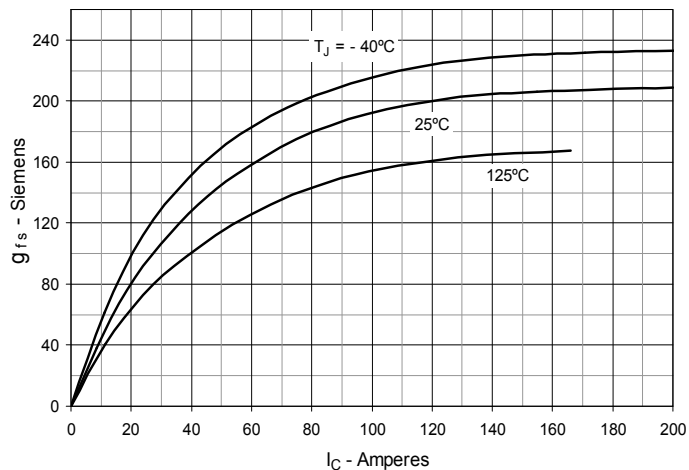
**Fig. 1. Output Characteristics**

 @  $T_J = 25^\circ\text{C}$ 

**Fig. 2. Extended Output Characteristics**

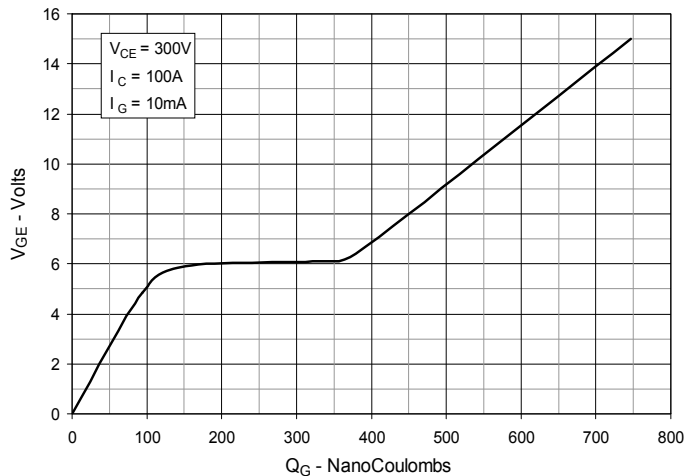
 @  $T_J = 25^\circ\text{C}$ 

**Fig. 3. Output Characteristics**

 @  $T_J = 125^\circ\text{C}$ 

**Fig. 4. Dependence of  $V_{CE(sat)}$  on**
**Junction Temperature**

**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**

**Fig. 6. Input Admittance**


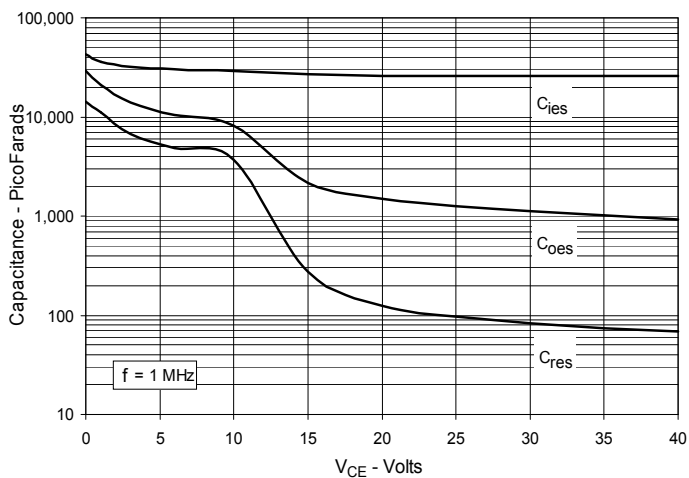
**Fig. 7. Transconductance**



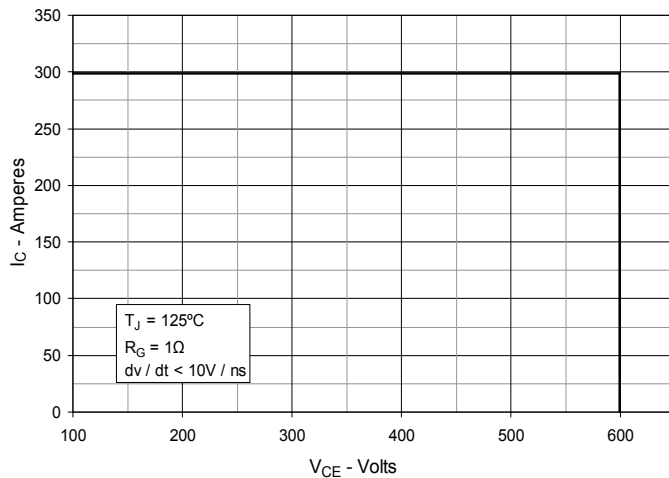
**Fig. 8. Gate Charge**



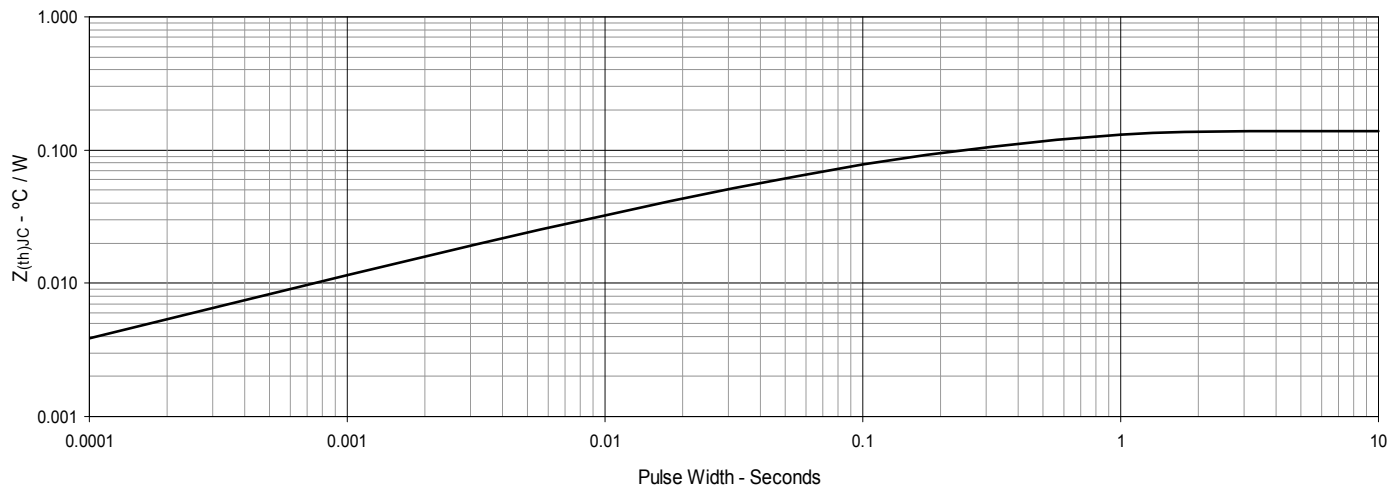
**Fig. 9. Capacitance**

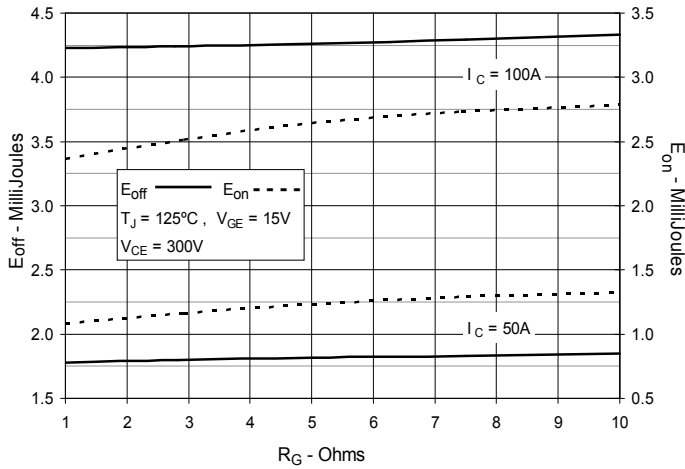
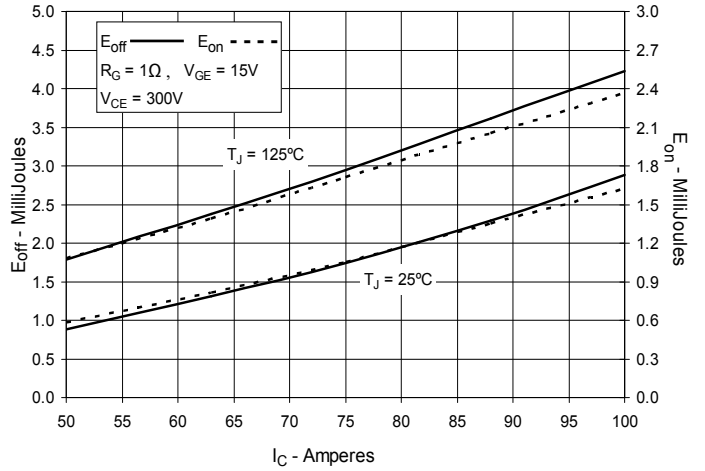
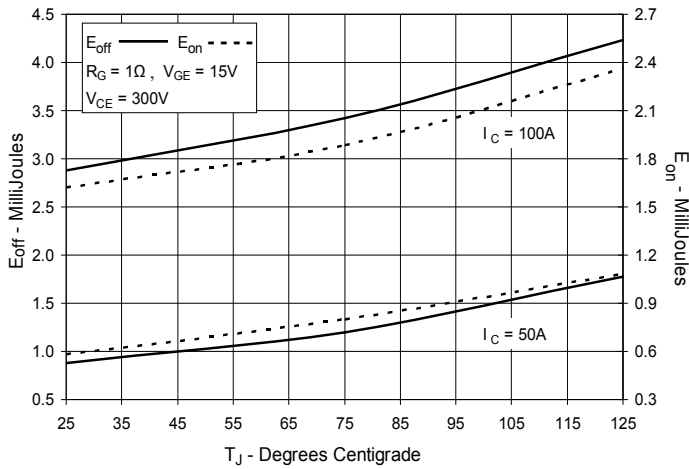
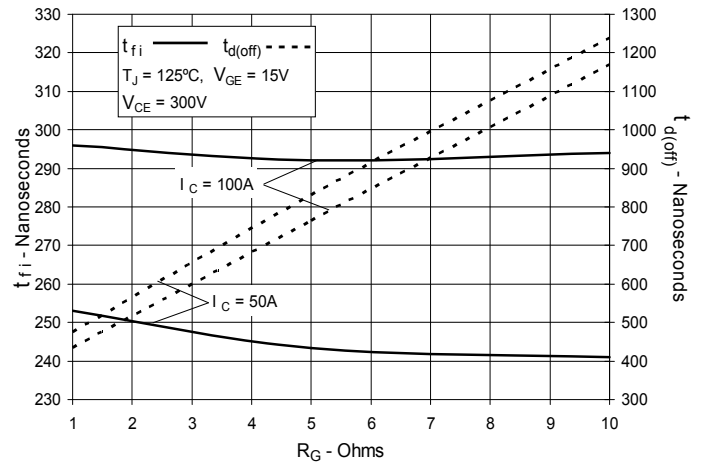
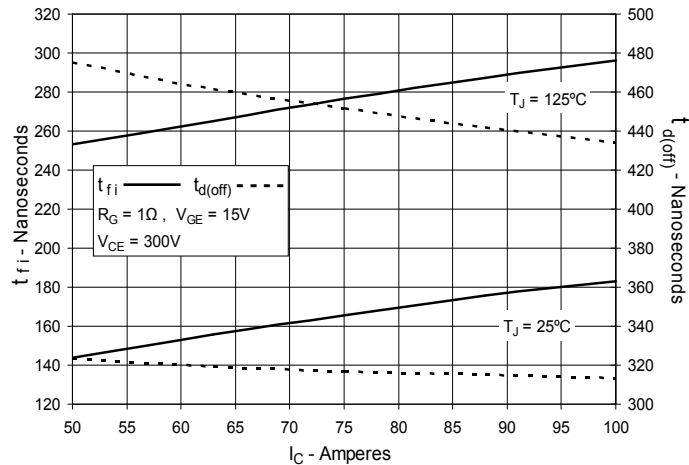
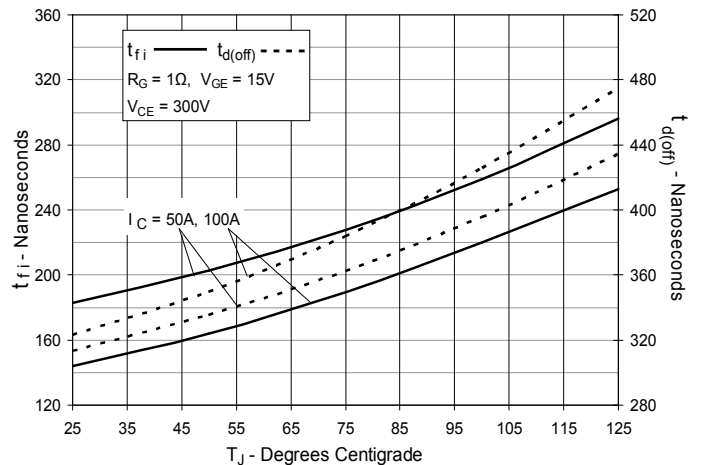


**Fig. 10. Reverse-Bias Safe Operating Area**

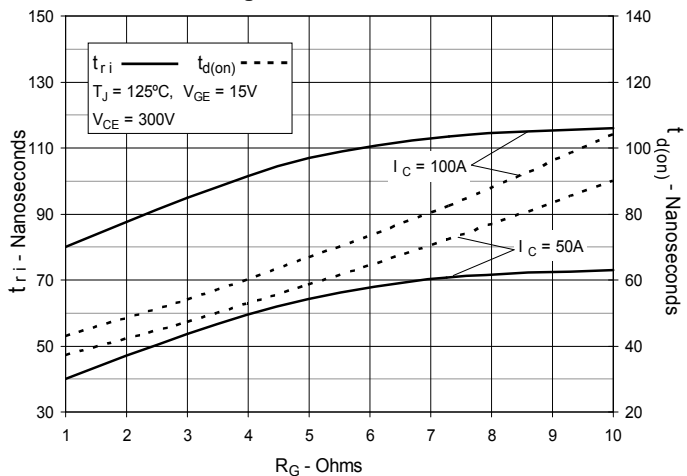


**Fig. 11. Maximum Transient Thermal Impedance**

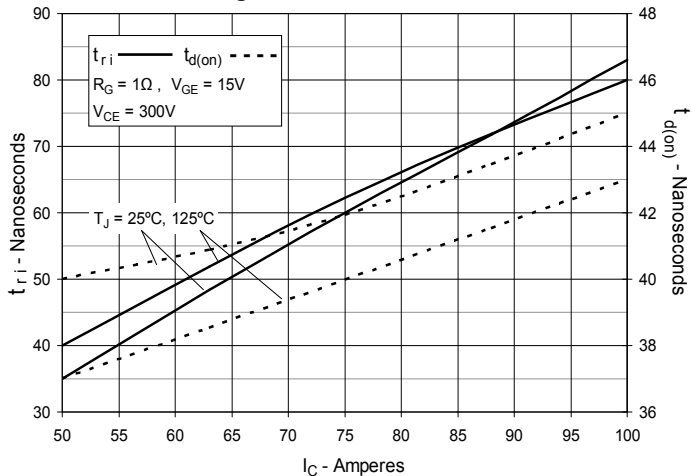


**Fig. 12. Inductive Switching  
Energy Loss vs. Gate Resistance**

**Fig. 13. Inductive Switching  
Energy Loss vs. Collector Current**

**Fig. 14. Inductive Switching  
Energy Loss vs. Junction Temperature**

**Fig. 15. Inductive Turn-off  
Switching Times vs. Gate Resistance**

**Fig. 16. Inductive Turn-off  
Switching Times vs. Collector Current**

**Fig. 17. Inductive Turn-off  
Switching Times vs. Junction Temperature**


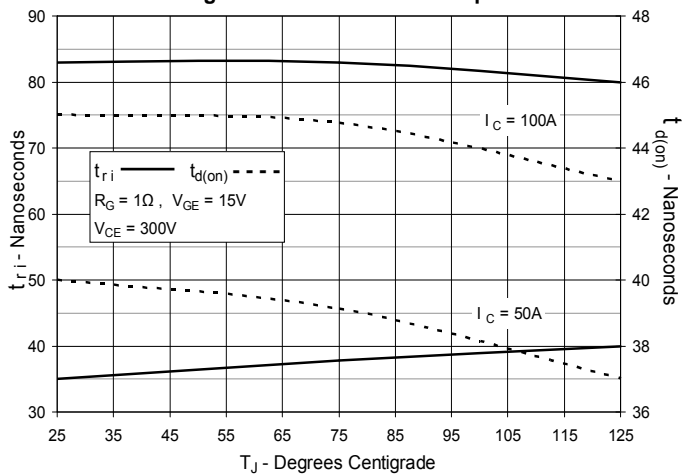
**Fig. 18. Inductive Turn-on  
Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on  
Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on  
Switching Times vs. Junction Temperature**



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